

Title (en)

Method of preparing a semiconductor substrate

Title (de)

Verfahren zur Herstellung eines Halbleitersubstrats

Title (fr)

Procédé de fabrication d'un substrat semi-conducteur

Publication

**EP 0553856 B1 20020417 (EN)**

Application

**EP 93101417 A 19930129**

Priority

- JP 4058492 A 19920131
- JP 4630392 A 19920131
- JP 4630492 A 19920131
- JP 4630592 A 19920131

Abstract (en)

[origin: EP0553856A2] A semiconductor substrate comprises an insulating layer and a compound semiconductor monocrystal thin film formed on said insulating layer, the thermal expansion coefficient of said insulating layer being in the range of 60%-140% of that of said monocrystal thin film.

IPC 1-7

**H01L 21/76**; **H01L 21/20**

IPC 8 full level

**H01L 21/20** (2006.01); **H01L 21/306** (2006.01); **H01L 21/762** (2006.01); **H01L 31/18** (2006.01)

CPC (source: EP US)

**H01L 21/02381** (2013.01 - EP US); **H01L 21/0245** (2013.01 - EP US); **H01L 21/02463** (2013.01 - EP US); **H01L 21/02507** (2013.01 - EP US); **H01L 21/02546** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 21/30604** (2013.01 - EP US); **H01L 21/76251** (2013.01 - EP US); **H01L 21/76256** (2013.01 - EP US); **H01L 31/1892** (2013.01 - EP US); **Y02E 10/50** (2013.01 - US); **Y10S 438/96** (2013.01 - EP US)

Cited by

EP1217663A1; EP1220330A1; EP0663688A3; US5695557A; US5980633A; US6602760B2; US6293149B1

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**EP 93101417 A 19930129**; DE 69331816 T 19930129; EP 01119915 A 19930129; US 30126394 A 19940906